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  - L4: (1504) 257/401.CCLS.3 and (field adj effect ad transistor "FET")
  - L5: (218) 4 and (ring annular)
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DBs: US-PPGPUB; USPAT; USOCR; EPO; JPO

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4 and (ring annular)

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| 62 | <input checked="" type="checkbox"/> | US 6509617 B2 | 20030121   |       | Semiconductor device and fabrication method thereof  | 257/409    | 257/355;<br>257/401;<br>257/E29.01.3; |
| 63 | <input checked="" type="checkbox"/> | US 6492691 B2 | 20021210   |       | High integration density MOS technology power device structure   | 257/401    | 257/339;<br>257/341;<br>257/409;      |
| 64 | <input type="checkbox"/>            | US 6489658 B2 | 20021203   | 6     | MOS-transistor for a photo cell  | 257/401    | 257/465;<br>257/466;<br>257/E27.1.32; |
| 65 | <input checked="" type="checkbox"/> | US 6448596 B1 | 20020910   | 40    | Solid-state imaging device   | 257/292    | 257/291;<br>257/401;<br>257/E27.1.32; |
| 66 | <input checked="" type="checkbox"/> | US 6445036 B1 | 20020903   | 16    | Semiconductor device having trench-structured rectangular unit cells   | 257/330    | 257/331;<br>257/335;<br>257/401;      |
| 67 | <input checked="" type="checkbox"/> | US 6420766 B1 | 20020716   | 43    | Transistor having raised source and drain  | 257/401    | 257/327;<br>257/622;<br>257/E21.027;  |
| 68 | <input checked="" type="checkbox"/> | US 6420757 B1 | 20020716   | 18    | Semiconductor diodes having low forward conduction voltage drop, low reverse current (akane... and hinh. avalanche. energy. canahimv. Hexagonal architecture | 257/341    | 257/401;<br>257/601;<br>257/E21.357;  |
| 69 | <input checked="" type="checkbox"/> | US 6407434 B1 | 20020618   | 136   |  | 257/401    | 257/207;<br>257/211;<br>257/758;      |
| 70 | <input checked="" type="checkbox"/> | US 6399991 B1 | 20020604   | 11    | Semiconductor integrated circuit   | 257/355    | 257/350;<br>257/360;<br>257/401;      |
| 71 | <input checked="" type="checkbox"/> | US 6359291 B1 | 20020319   | 24    | Corrosion resistant imager   | 257/72     | 257/401;<br>257/763;<br>257/765;      |
| 72 | <input checked="" type="checkbox"/> | US 6326656 B1 | 20011204   | 5     | Lateral high-voltage transistor  | 257/288    | 257/339;<br>257/345;<br>257/355;      |